Antonio Polimeni

List of Publications by Citations

231 papers	4,072 citations	36 h-index	50 g-index
249 ext. papers	4,481 ext. citations	4.5 avg, IF	4.89 L-index

#	Paper	IF	Citations
231	Temperature dependence of the optical properties of InAs/AlyGa1−yAs self-organized quantum dots. *Physical Review B*, **1999**, 59, 5064-5068	3.3	196
230	Effect of temperature on the optical properties of (InGa)(AsN)/GaAs single quantum wells. *Applied Physics Letters*, **2000**, 77, 2870-2872	3.4	105
229	Interaction between conduction band edge and nitrogen states probed by carrier effective-mass measurements in GaAs1−xNx. *Physical Review B*, **2006**, 73,	3.3	101
228	Effect of hydrogen on the electronic properties of InxGa1−xAs1−yNy/GaAs quantum wells. *Physical Review B*, **2001**, 63,	3.3	92
227	Influence of bismuth incorporation on the valence and conduction band edges of GaAs1−xBix. *Applied Physics Letters*, **2008**, 92, 262105	3.4	86
226	Trends in the electronic structure of dilute nitride alloys. *Semiconductor Science and Technology*, **2009**, 24, 033001	1.8	84
225	Hydrogen-induced band gap tuning of (InGa)(AsN)/GaAs single quantum wells. *Applied Physics Letters*, **2001**, 78, 3472-3474	3.4	81
224	Electronic structure of self-assembled InAs quantum dots in GaAs matrix. *Applied Physics Letters*, **1998**, 73, 1092-1094	3.4	79
223	Effect of nitrogen on the temperature dependence of the energy gap in InxGa1−xAs1−yNy/GaAs single quantum wells. *Physical Review B*, **2001**, 63,	3.3	67
222	Linewidth analysis of the photoluminescence of InxGa1-xAs/GaAs quantum wells (x=0.09, 0.18, 1.0). *Physical Review B*, **1995**, 52, 2784-2788	3.3	61
221	Nitrogen-hydrogen complex in GaAsxN1−x revealed by x-ray absorption spectroscopy. *Physical Review B*, **2005**, 71,	3.3	55
220	Self-aggregation of quantum dots for very thin InAs layers grown on GaAs. *Physical Review B*, **1996**, 53, R4213-R4216	3.3	55
219	Evidence of the direct-to-indirect band gap transition in strained two-dimensional WS2, MoS2, and WSe2. *Physical Review Research*, **2020**, 2,	3.9	55
218	Early manifestation of localization effects in diluted Ga(AsN). *Applied Physics Letters*, **2003**, 82, 4474-4476	3.4	53
217	Nitrogen passivation induced by atomic hydrogen: The GaP1−yNy case. *Physical Review B*, **2003**, 67,	3.3	51
216	Structure and passivation effects of mono- and dihydrogen complexes in GaAsyN(1-y) alloys. *Physical Review Letters*, **2002**, 89, 216401	7.4	50
215	Compositional dependence of the exciton reduced mass in GaAs1−xBix (x=0–10%). *Physical Review B*, **2010**, 81,	3.3	48

214	In-Plane Bandgap Engineering by Modulated Hydrogenation of Dilute Nitride Semiconductors. *Advanced Materials*, **2006**, 18, 1993-1997	24	48
213	Optical properties and device applications of (InGa)As self-assembled quantum dots grown on (311)B GaAs substrates. *Applied Physics Letters*, **1998**, 73, 1415-1417	3.4	46
212	Hydrogen-induced improvements in optical quality of GaNAs alloys. *Applied Physics Letters*, **2003**, 82, 3662-3664	3.4	45
211	Effect of the order-disorder transition on the optical properties of Cu2ZnSnS4. *Applied Physics Letters*, **2016**, 108, 211909	3.4	44
210	Influence of nitrogen-cluster states on the gyromagnetic factor of electrons in GaAs1□Nx. *Physical Review B*, **2006**, 74,	3.3	43
209	Piezoelectric effects in In0.5Ga0.5As self-assembled quantum dots grown on (311)B GaAs substrates. *Applied Physics Letters*, **2000**, 77, 2979-2981	3.4	43
208	Temperature Dependence of Interband Transitions in Wurtzite InP Nanowires. *ACS Nano*, **2015**, 9, 4277-87	13.7	40
207	Vibrational spectroscopy of hydrogenated GaAs1□Ny: A structure-sensitive test of an H2*(N) model. *Physical Review B*, **2004**, 69,	3.3	40
206	Global changes of the band structure and the crystal lattice of Ga(N,As) due to hydrogenation. *Physical Review B*, **2003**, 67,	3.3	39
205	High-temperature light emission from InAs quantum dots. *Applied Physics Letters*, **1999**, 75, 814-816	3.4	39
204	Polarized light absorption in wurtzite InP nanowire ensembles. *Nano Letters*, **2015**, 15, 998-1005	11.5	38
203	Fabrication of site-controlled quantum dots by spatially selective incorporation of hydrogen in Ga(AsN)/GaAs heterostructures. *Advanced Materials*, **2011**, 23, 2706-10	24	38
202	Electron mass in dilute nitrides and its anomalous dependence on hydrostatic pressure. *Physical Review Letters*, **2007**, 98, 146402	7.4	38
201	Tunable variation of the electron effective mass and exciton radius in hydrogenated GaAs1□Nx. *Physical Review B*, **2004**, 69,	3.3	38
200	Magnetophotoluminescence studies of (InGa)(AsN)/GaAs heterostructures. *Physical Review B*, **2003**, 67,	3.3	38
199	Bandgap Energy of Wurtzite InAs Nanowires. *Nano Letters*, **2016**, 16, 5197-203	11.5	37
198	Formation and dissolution of D-N complexes in dilute nitrides. *Physical Review B*, **2007**, 76,	3.3	37
197	Defect passivation in strain engineered InAs/(InGa)As quantum dots. *Materials Science and Engineering C*, **2005**, 25, 830-834	8.3	37

196	Lattice relaxation by atomic hydrogen irradiation of III□N□V semiconductor alloys. *Physical Review B* , **2003**, 68,	3.3	36
195	Bi-induced p-type conductivity in nominally undoped Ga(AsBi). *Applied Physics Letters*, **2012**, 100, 092109	3.4	35
194	Thermal effects in quantum dot lasers. *Journal of Applied Physics*, **1999**, 85, 625-627	2.5	35
193	Long-Lived Hot Carriers in III-V Nanowires. *Nano Letters*, **2016**, 16, 3085-93	11.5	35
192	Hydrogen-nitrogen complexes in dilute nitride alloys: Origin of the compressive lattice strain. *Applied Physics Letters*, **2006**, 89, 061904	3.4	34
191	Carrier thermalization within a disordered ensemble of self-assembled quantum dots. *Physical Review B*, **2000**, 62, 11084-11088	3.3	33
190	Experimental evidence of different hydrogen donors in n-type InN. *Physical Review B*, **2008**, 77,	3.3	32
189	Quantum-dot phonons in self-assembled InAs/GaAs quantum dots: Dependence on the coverage thickness. *Applied Physics Letters*, **2000**, 77, 3556-3558	3.4	32
188	Stokes shift in quantum wells: Trapping versus thermalization. *Physical Review B*, **1996**, 54, 16389-16392	3.3	32
187	Controlled Micro/Nanodome Formation in Proton-Irradiated Bulk Transition-Metal Dichalcogenides. *Advanced Materials*, **2019**, 31, e1903795	24	31
186	Excitonic recombination and absorption in InxGa1□As/GaAs heterostructure nanowires. *Physical Review B*, **2013**, 87,	3.3	31
185	Compositional evolution of Bi-induced acceptor states in GaAs1□Bix alloy. *Physical Review B*, **2011**, 83,	3.3	31
184	Emission of electrons from the ground and first excited states of self-organized InAs/GaAs quantum dot structures. *Journal of Electronic Materials*, **1999**, 28, 486-490	1.9	31
183	InAs quantum dots grown on nonconventionally oriented GaAs substrates. *Journal of Crystal Growth*, **1998**, 187, 126-132	1.6	30
182	Temperature dependence and bowing of the bandgap in ZnSe1□Ox. *Applied Physics Letters*, **2004**, 84, 3304-3306	3.4	30
181	Single photons on demand from novel site-controlled GaAsN/GaAsN:H quantum dots. *Nano Letters*, **2014**, 14, 1275-80	11.5	28
180	Role of hydrogen in III□N□V compound semiconductors. *Semiconductor Science and Technology*, **2002**, 17, 797-802	1.8	27
179	Photoreflectance and reflectance investigation of deuterium-irradiated GaAsN. *Applied Physics Letters*, **2007**, 90, 091907	3.4	26

178	Indium interdiffusion in annealed and implanted InAs/(AlGa)As self-assembled quantum dots. *Journal of Applied Physics*, **2001**, 89, 6044-6047	2.5	25
177	Self-aggregated InAs quantum dots in GaAs. *Journal of Applied Physics*, **1998**, 83, 5529-5535	2.5	25
176	Influence of high-index GaAs substrates on the growth of highly strained (InGa)As/GaAs heterostructures. *Journal of Crystal Growth*, **1999**, 201-202, 276-279	1.6	25
175	Exciton localization by potential fluctuations at the interface of InGaAs/GaAs quantum wells. *Physical Review B*, **1996**, 53, 7421-7425	3.3	25
174	Giant photoluminescence enhancement in deuterated highly strained InAs/GaAs quantum wells. *Applied Physics Letters*, **1994**, 65, 1254-1256	3.4	25
173	Hydrogen Incorporation in III-N-V Semiconductors: From Macroscopic to Nanometer Control of the Materials Physical Properties. *Advanced Functional Materials*, **2012**, 22, 1782-1801	15.6	24
172	Laser Level Scheme of Self-Interstitials in Epitaxial Ge Dots Encapsulated in Si. *Nano Letters*, **2016**, 16, 6802-6807	11.5	24
171	Hydrogen diffusion in GaAs1 Nx. *Physical Review B*, **2009**, 80,	3.3	23
170	Carrier mass measurements in degenerate indium nitride. *Physical Review B*, **2009**, 79,	3.3	23
169	Spectral analysis of InGaAs/GaAs quantum-dot lasers. *Applied Physics Letters*, **1999**, 75, 2169-2171	3.4	23
168	Reduced temperature dependence of the band gap in GaAs1 Ny investigated with photoluminescence. *Physical Review B*, **2002**, 65,	3.3	22
167	Hydrogen-induced passivation of nitrogen in GaAs1 Ny. *Physical Review B*, **2002**, 65,	3.3	22
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165	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties of GaNxP1 alloys: A proof for a general property of dilute nitrides. *Physical Review B*, **2004**, 70,	3.3	21
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163	High-resolution X-ray diffractionin situstudy of very small complexes: the case of hydrogenated dilute nitrides. *Journal of Applied Crystallography*, **2008**, 41, 366-372	3.8	20
162	Passivation of an isoelectronic impurity by atomic hydrogen: The case of ZnTe:O. *Applied Physics Letters*, **2006**, 88, 101910	3.4	20
161	Free carrier and/or exciton trapping by nitrogen pairs in dilute GaP1 Nx. *Physical Review B*, **2005**, 71,	3.3	20

160	Resonant tunneling and photoluminescence spectroscopy in quantum wells containing self-assembled quantum dots. *Journal of Applied Physics*, **2000**, 88, 2005-2012	2.5	20
159	Effective phonon bottleneck in the carrier thermalization of InAs/GaAs quantum dots. *Physical Review B*, **2008**, 78,	3.3	19
158	Vibrational properties of the H-N-H complex in dilute III-N-V alloys: Infrared spectroscopy and density functional theory. *Physical Review B*, **2008**, 77,	3.3	19
157	Photoreflectance evidence of the N-induced increase of the exciton binding energy in an InxGa1−xAs1−yNy alloy. *Applied Physics Letters*, **2003**, 83, 470-472	3.4	19
156	Local structure of nitrogen-hydrogen complexes in dilute nitrides. *Physical Review B*, **2009**, 79,	3.3	18
155	Role of N clusters in InxGa1−xAs1−yNy band-gap reduction. *Physical Review B*, **2002**, 66,	3.3	18
154	Modulation of the luminescence spectra of InAs self-assembled quantum dots by resonant tunneling through a quantum well. *Physical Review B*, **2000**, 62, 13595-13598	3.3	18
153	Detailed structure of the H-N-H center in GaAsyN1−y revealed by vibrational spectroscopy under uniaxial stress. *Physical Review B*, **2010**, 81,	3.3	17
152	Ferromagnetism and Conductivity in Hydrogen Irradiated Co-Doped ZnO Thin Films. *ACS Applied Materials & Interfaces*, **2016**, 8, 12925-31	9.5	17
151	Electronic properties of wurtzite-phase InP nanowires determined by optical and magneto-optical spectroscopy. *Applied Physics Reviews*, **2017**, 4, 041102	17.3	16
150	Light polarization control in strain-engineered GaAsN/GaAsN:H heterostructures. *Applied Physics Letters*, **2009**, 94, 261905	3.4	16
149	Band-gap profiling by laser writing of hydrogen-containing III-N-Vs. *Physical Review B*, **2012**, 86,	3.3	16
148	Engineered Creation of Periodic Giant, Nonuniform Strains in MoS2 Monolayers. *Advanced Materials Interfaces*, **2020**, 7, 2000621	4.6	15
147	Determination of exciton reduced mass and gyromagnetic factor of wurtzite (InGa)As nanowires by photoluminescence spectroscopy under high magnetic fields. *ACS Nano*, **2013**, 7, 10717-25	16.7	15
146	Effects of Bi incorporation on the electronic properties of GaAs: Carrier masses, hole mobility, and Bi-induced acceptor states. *Physica Status Solidi (B): Basic Research*, **2013**, 250, 779-786	1.3	15
145	Evolution of the Optical Properties of InAs/GaAs Quantum Dots for Increasing InAs Coverages. *Physica Status Solidi A*, **1997**, 164, 493-497		15
144	Role of strain and properties of N clusters at the onset of the alloy limit in GaAs1−xNx. *Physical Review B*, **2008**, 77,	3.3	15
143	High temperature photoluminescence efficiency and thermal stability of (InGa)(AsN)/GaAs quantum wells. *Applied Physics Letters*, **2001**, 79, 2585-2587	3.4	15

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141	Characteristics of InN grown on SiC under the In-rich regime by molecular beam heteroepitaxy. *Applied Physics Letters*, **2007**, 90, 011910	3.4	14
140	Substrate orientation dependence of island nucleation critical thickness in strained heterostructures. *Europhysics Letters*, **1999**, 47, 701-707	1.6	14
139	Value and Anisotropy of the Electron and Hole Mass in Pure Wurtzite InP Nanowires. *Nano Letters*, **2016**, 16, 6213-6221	11.5	14
138	Microscopic origin of compressive strain in hydrogen-irradiated dilute GaAs1−yNy alloys: Role of N-Hn centers with n>2 and their thermal stability. *Physical Review B*, **2012**, 86,	3.3	13
137	Role of the host matrix in the carrier recombination of InGaAsN alloys. *Applied Physics Letters*, **2003**, 82, 2805-2807	3.4	13
136	Experimental studies of the multimode spectral emission in quantum dot lasers. *Journal of Applied Physics*, **2000**, 87, 1943-1946	2.5	13
135	Photoluminescence spectroscopy of self-assembled (InGa)As quantum dots in high magnetic fields. *Physica B: Condensed Matter*, **1998**, 249-251, 262-266	2.8	12
134	Effect of hydrogen incorporation temperature in in plane-engineered GaAsN□GaAsN:H heterostructures. *Applied Physics Letters*, **2008**, 92, 221901	3.4	12
133	Nitrogen-induced perturbation of the valence band states in GaP1−xNx alloys. *Physical Review B*, **2006**, 74,	3.3	12
132	Exciton confinement in GaAs quantum barriers. *Physical Review B*, **1993**, 48, 1643-1646	3.3	12
131	Resonant depletion of photogenerated carriers in InGaAs/GaAs nanowire mats. *Applied Physics Letters*, **2013**, 102, 173102	3.4	11
130	Compositional disorder in GaAs1−xNx:H investigated by photoluminescence. *Physical Review B*, **2006**, 74,	3.3	11
129	Broadband enhancement of light-matter interaction in photonic crystal cavities integrating site-controlled quantum dots. *Physical Review B*, **2020**, 101,	3.3	10
128	Carrier masses and band-gap temperature sensitivity in Ga(AsBi) alloys. *Semiconductor Science and Technology*, **2015**, 30, 094002	1.8	10
127	Binding Energy and Lifetime of Excitons in InxGa1−xAs/GaAs Quantum Wells. *Physica Status Solidi A*, **1997**, 164, 107-110		10
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125	Effects of hydrogenation on the local structure of InxGa1−xAs1−yNy quantum wells and GaAs1−yNy epilayers. *Physical Review B*, **2005**, 72,	3.3	10

124	Comparison between experimental and theoretical determination of the local structure of the GaAs1−yNy dilute nitride alloy. *Physical Review B*, **2005**, 71,	3.3	10
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121	Intra-shell transitions of 3D metal ions (Fe, Co, Ni) in II-VI wide-gap semiconductor alloys. *Physica B: Condensed Matter*, **1999**, 273-274, 848-851	2.8	10
120	Photoinduced structures in the exciton luminescence spectrum of InGaAs/GaAs quantum well heterostructures. *Journal of Applied Physics*, **1996**, 80, 3011-3016	2.5	10
119	A lithographic approach for quantum dot-photonic crystal nanocavity coupling in dilute nitrides. *Microelectronic Engineering*, **2017**, 174, 16-19	2.5	9
118	Addressing the Fundamental Electronic Properties of Wurtzite GaAs Nanowires by High-Field Magneto-Photoluminescence Spectroscopy. *Nano Letters*, **2017**, 17, 6540-6547	11.5	9
117	Giant magneto-optical response in H+ irradiated Zn1−xCoxO thin films. *Journal of Materials Chemistry C*, **2019**, 7, 78-85	7.1	9
116	Unusual spin properties of InP wurtzite nanowires revealed by Zeeman splitting spectroscopy. *Physical Review B*, **2019**, 99,	3.3	9
115	Azetidinium lead iodide: synthesis, structural and physico-chemical characterization. *Journal of Materials Chemistry A*, **2018**, 6, 10135-10148	13	9
114	Site-Controlled Quantum Emitters in Dilute Nitrides and their Integration in Photonic Crystal Cavities. *Photonics*, **2018**, 5, 10	2.2	9
113	Hydrogen effects in dilute III-N-V alloys: From defect engineering to nanostructuring. *Journal of Applied Physics*, **2014**, 115, 012011	2.5	9
112	Nanoscale Tailoring of the Polarization Properties of Dilute-Nitride Semiconductors via H-Assisted Strain Engineering. *Physical Review Applied*, **2014**, 2,	4.3	9
111	Optical study of hydrogen-irradiated GaAsN/GaAs heterostructures. *Journal of Applied Physics*, **2011**, 109, 123511	2.5	9
110	Effects of hydrogen on the electronic properties of Ga(AsBi) alloys. *Applied Physics Letters*, **2012**, 101, 222103	3.4	9
109	Spectroscopic studies of self-assembled InAs and In0.5Ga0.5As quantum dots. *Applied Surface Science*, **1998**, 123-124, 366-370	6.7	9
108	In-plane band gap modulation investigated by secondary electron imaging of GaAsN/GaAsN:H heterostructures. *Applied Physics Letters*, **2008**, 93, 102116	3.4	9
107	Photoreflectance investigation of hydrogenated (InGa)(AsN)/GaAs heterostructures. *European Physical Journal B*, **2002**, 30, 39-43	1.2	9

106	Nanoscale Measurements of Elastic Properties and Hydrostatic Pressure in H2-Bulged MoS2 Membranes. *Advanced Materials Interfaces*, **2020**, 7, 2001024	4.6	9
105	The Interaction of Hydrogen with the van der Waals Crystal -InSe. *Molecules*, **2020**, 25,	4.8	8
104	InP-InGaAs core-multi-shell nanowire quantum wells with tunable emission in the 1.3-1.55 μm wavelength range. *Nanoscale*, **2017**, 9, 13554-13562	7.7	8
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102	Giant and reversible enhancement of the electrical resistance of GaAs1−xNx by hydrogen irradiation. *Physical Review B*, **2011**, 84,	3.3	8
101	Deep levels in H-irradiated GaAs1-xNx (x . *Journal of Applied Physics*, **2011**, 110, 124508	2.5	8
100	Identification of four-hydrogen complexes in In-rich InxGa1−xN (x>0.4) alloys using photoluminescence, x-ray absorption, and density functional theory. *Physical Review B*, **2012**, 86,	3.3	8
99	Characterization of hydrogen passivated defects in strain-engineered semiconductor quantum dot structures. *Journal of Applied Physics*, **2006**, 100, 084313	2.5	8
98	Behavior of hydrogen in InN investigated in real time exploiting spectroscopic ellipsometry. *Applied Physics Letters*, **2007**, 91, 081917	3.4	8
97	Carrier relaxation dynamics in annealed and hydrogenated (GaIn)(NAs)/GaAs quantum wells. *Applied Physics Letters*, **2005**, 87, 252111	3.4	8
96	Atomic ordering in (InGa)(AsN) quantum wells: An In K-edge X-ray absorption investigation. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 200, 34-39	1.2	8
95	Emission energy and polarization tuning of InAs/GaAs self-assembled quantum dots by growth interruption. *Journal of Crystal Growth*, **2003**, 251, 192-195	1.6	8
94	Optical and morphological properties of In(Ga)As/GaAs quantum dots grown on novel index surfaces. *Microelectronics Journal*, **1999**, 30, 419-425	1.8	8
93	Common nonlinear features and spin-orbit coupling effects in the Zeeman splitting of novel wurtzite materials. *Physical Review B*, **2019**, 99,	3.3	7
92	Laser writing of the electronic activity of N- and H-atoms in GaAs. *Applied Physics Letters*, **2011**, 99, 021105	3.4	7
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90	Effect of postgrowth hydrogen treatment on defects in GaNP. *Applied Physics Letters*, **2011**, 98, 141920	3.4	7
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88	Universality of the Stokes Shift for a Disordered Ensemble of Quantum Dots. *Physica Status Solidi (B): Basic Research*, **2001**, 224, 41-45	1.3	7
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84	High field magnetoluminescence spectroscopy of self-assembled (InGa)As quantum dots on high index planes. *Physica B: Condensed Matter*, **1998**, 246-247, 93-96	2.8	6
83	Electron and hole levels of InAs quantum dots in a GaAs matrix. *Superlattices and Microstructures*, **1999**, 25, 105-111	2.8	6
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79	In-Situ Annealing and Hydrogen Irradiation of Defect-Enhanced Germanium Quantum Dot Light Sources on Silicon. *Crystals*, **2020**, 10, 351	2.3	5
78	Connections between local and macroscopic properties in solids: The case of N in III-V-N alloys. *Physical Review B*, **2014**, 89,	3.3	5
77	Genesis of Solitary Cations Induced by Atomic Hydrogen. *Advanced Functional Materials*, **2015**, 25, 5353-5359	15.1	5
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75	An all optical mapping of the strain field in GaAsN/GaAsN:H wires. *Applied Physics Letters*, **2012**, 101, 191908	3.4	5
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73	Above barrier exciton confinement in InGaAs/GaAs multiple-quantum-well structures. *Solid-State Electronics*, **1994**, 37, 641-644	1.7	5
72	Deuterium Adsorption on Free-Standing Graphene. *Nanomaterials*, **2021**, 11,	5.4	5
71	Plasmon-assisted bandgap engineering in dilute nitrides. *Nanophotonics*, **2019**, 8, 1465-1476	6.3	4

70	H-tailored surface conductivity in narrow band gap In(AsN). *Applied Physics Letters*, **2015**, 106, 022111	3.4	4
69	Spatially selective hydrogen irradiation of dilute nitride semiconductors: a brief review. *Semiconductor Science and Technology*, **2018**, 33, 053001	1.8	4
68	Local magneto-optical response of H+ irradiated Zn1−xCoxO thin films. *European Physical Journal: Special Topics*, **2019**, 228, 683-687	2.3	4
67	Peculiarities of the hydrogenated In(AsN) alloy. *Semiconductor Science and Technology*, **2015**, 30, 105030	1.8	4
66	Effects of hydrogenation on non-radiative defects in GaNP and GaNAs alloys: An optically detected magnetic resonance study. *Journal of Applied Physics*, **2012**, 111, 023501	2.5	4
65	Formation and relaxation of exciton-carbon acceptor complexes in GaAs. *Physical Review B*, **1997**, 56, 3834-3837	3.3	4
64	Interplay of nitrogen and hydrogen in InxGa1−xAs1−yNy/GaAs heterostructures. *Physica B: Condensed Matter*, **2001**, 308-310, 850-853	2.8	4
63	Piezoelectric Effects on the Electron–Hole Dipole in In0.5Ga0.5As/GaAs Self-Assembled Quantum Dots. *Physica Status Solidi (B): Basic Research*, **2001**, 224, 37-40	1.3	4
62	Self-assembling of In(Ga)As/GaAs quantum dots on (N11) substrates: the (311)A case. *Micron*, **2000**, 31, 309-13	2.3	4
61	Exceptional Elasticity of Microscale Constrained MoS Domes. *ACS Applied Materials & Interfaces*, **2021**, 13, 48228-48238	9.5	4
60	Synchrotron x-ray diffraction study of micro-patterns obtained by spatially selective hydrogenation of GaAsN. *Applied Physics Letters*, **2015**, 106, 051905	3.4	3
59	H irradiation effects on the GaAs-like Raman modes in GaAs1-xNx/GaAs1-xNx:H planar heterostructures. *Journal of Applied Physics*, **2014**, 116, 245304	2.5	3
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